

<p style="text-align: center;">Substitute for form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i></p>				<i>Complete if Known</i>			
				Application Number		<b>10/566522</b>	
				Filing Date			
				First Named Inventor		Yoshito Jin	
				Art Unit		10550522 - GAU: 2894	
				Examiner Name		/Jami Valentine/	
Sheet	1	of	2	Attorney Docket Number	<b>096790 . P520</b>		

<b>U.S.PATENT DOCUMENT</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
		US 3,795,977		3/12/1974	Berkenflit et al.
		US			
		US			

<b>FOREIGN PATENT DOCUMENT</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document
		Country Code <sup>3</sup>	Number <sup>4</sup>	KindCode <sup>5</sup> (if known)	
		JP	08-031960	A	02-02-1996 MATSUSHITA ELECTRIC IND CO LTD
		JP	10-152397	A	06-09-1998 NIPPON TELEGRAPH & TELEPHONE CORP
		JP	10-152398	A	06-09-1998 NIPPON TELEGR & TELEPH CORP
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		JP	08-306806	A	11-22-1996 ASAHI CHEM IND CO LTD
		JP	07-263646	A	10-13-1995 MITSUBISHI CHEM CORP
		JP	08-161933	A	06-21-1996 SHARP CORP
		JP	50-004986	A	01-20-1975 INTERNATIONAL BUSINESS MACHINES CORP
		JP	49-034390	B	09-13-1974 MATSUSHITA ELECTRIC IND CO LTD

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<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov), MPEP901.04 or in the comment box of this document. <sup>3</sup>Enter office that issued the document, by the two-letter code (WIPO Standard ST.3) <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to indicate here if English language Translation is attached.

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /JMV/

Substitute for form 1449B/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i> <b>10/566522</b> Application Number      10566522 - GAU: 2894 Filing Date First Named Inventor      Yoshito Jin Art Unit Examiner Name      /Jami Valentine/ Sheet <b>2</b> of <b>2</b> Attorney Docket Number      096790.P520	
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<b>OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS</b>				
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		Translation <sup>2</sup>
		Sze, "Physics of Semiconductor Devices", Jhon Wiley and Sons, Inc., 1981		
		Matsuoka, "Applied Physics", Vol. 73, No. 9, pp.1166, 2004		Abstract
		"Development and Application of Ferroelectric Materials", edited by Tadashi Shiosaki, CMC Co., Ltd.		Abstract
		Inomata et al., "MRM Technology – from Fundamentals to LSI Applications", SIPEC		Abstract
		Amazawa et al., "Ultrathin oxidefilms deposited using electron cyclotron resonance sputter", J. Vac. Sci. Technol., B 17, No. 5		
		Matsuoka et al., "Low-temperature epitaxial growth of BaTiO <sub>3</sub> films by radio-frequency-mode electron cyclotron resonance sputtering", J. Appl. Phys., 76(3), 1768 (1994)		
		Watazu et al., "Powder and Powder Metallurgy", No. 44, pp. 86, 1997		Abstract
		Masumoto et al., "Preparation of Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> films on a single-crystal sapphire substrate with electron cyclotron resonance plasma sputtering", Appl. Phys. Lett., 58, 243 (1991)		
		Yamaguchi et al., "Effect of Grain Size on Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> Thin Film Properties", Jpn. J. Appl. Phys., Vol. 37, (1998) pp. 5166 – 5170		
		Wild et al., "Hafnium and Zirconium silicates for advanced gate dielectrics", J. Appl. Phys., Vol. 87, No. 1, January 2000, pp. 484 – 492		

Examiner Signature	/Jami Valentine/	Date Considered	12/17/2008
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